Complementary Silicon Plastic Power Transistors

DPAK-3 for Surface Mount Applications

Designed for low voltage, low-power, high-gain audio amplifier applications.

Features

- High DC Current Gain
- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Low Collector-Emitter Saturation Voltage
- High Current-Gain Bandwidth Product
- Annular Construction for Low Leakage
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{CB}	100	Vdc
Collector-Emitter Voltage	V _{CEO}	100	Vdc
Emitter-Base Voltage	V _{EB}	7.0	Vdc
Collector Current – Continuous	I _C	4.0	Adc
Collector Current – Peak	I _{CM}	8.0	Adc
Base Current	I _B	1.0	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	12.5 0.1	W W/°C
Total Device Dissipation @ T _A = 25°C (Note 2) Derate above 25°C	P _D	1.4 0.011	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C
ESD – Human Body Model	HBM	3B	V
ESD – Machine Model	MM	С	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. When surface mounted on minimum pad sizes recommended.

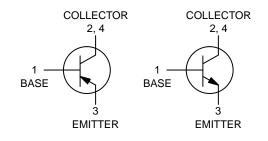


ON Semiconductor®

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4.0 A, 100 V, 12.5 W POWER TRANSISTOR

COMPLEMENTARY



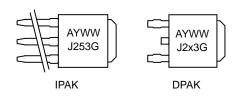


IPAK CASE 369D STYLE 1



DPAK-3 CASE 369C STYLE 1

MARKING DIAGRAMS



A = Assembly Location

Y = Year WW = Work Week x = 4 or 5

G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance Junction-to-Case Junction-to-Ambient (Note 2)	R _{θJC} R _{θJA}	10 89.3	°C/W

^{2.} When surface mounted on minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	,		•	•
Collector–Emitter Sustaining Voltage (Note 3) $(I_C = 10 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	100	-	Vdc
Collector Cutoff Current $(V_{CB} = 100 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 100 \text{ Vdc}, I_E = 0, T_J = 125^{\circ}\text{C})$	I _{CBO}	- -	100 100	nAdc μAdc
Emitter Cutoff Current (V _{BE} = 7.0 Vdc, I _C = 0)	I _{EBO}	-	100	nAdc
DC Current Gain (Note 3) ($I_C = 200 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 1.0 \text{ Adc}, V_{CE} = 1.0 \text{ Vdc}$)	h _{FE}	40 15	180	-
Collector–Emitter Saturation Voltage (Note 3) ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$) ($I_C = 1.0 \text{ Adc}$, $I_B = 100 \text{ mAdc}$)	V _{CE(sat)}	-	0.3 0.6	Vdc
Base–Emitter Saturation Voltage (Note 3) (I _C = 2.0 Adc, I _B = 200 mAdc)	V _{BE(sat)}	-	1.8	Vdc
Base–Emitter On Voltage (Note 3) (I _C = 500 mAdc, V _{CE} = 1.0 Vdc)	V _{BE(on)}	-	1.5	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain - Bandwidth Product (Note 4) (I _C = 100 mAdc, V _{CE} = 10 Vdc, f _{test} = 10 MHz)	f _T	40	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz)	C _{ob}		50	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \approx 2%.

^{4.} $f_T = |h_{FE}| \cdot f_{test}$.

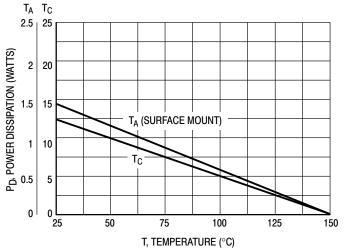


Figure 1. Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

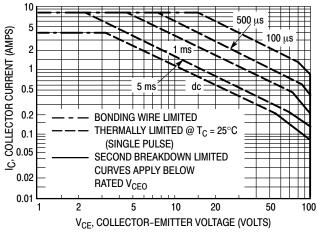


Figure 2. Active Region Maximum Safe Operating Area

The data of Figure 2 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 3. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

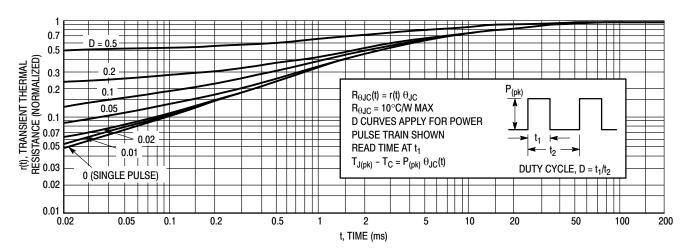


Figure 3. Thermal Response

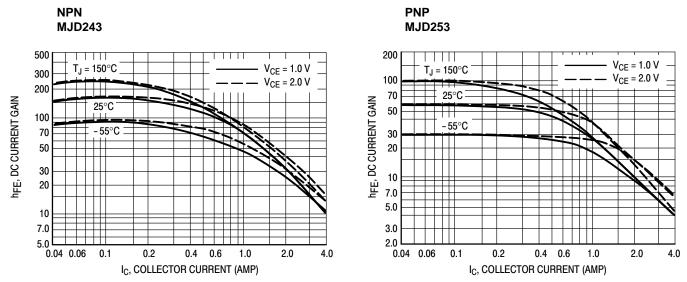


Figure 4. DC Current Gain

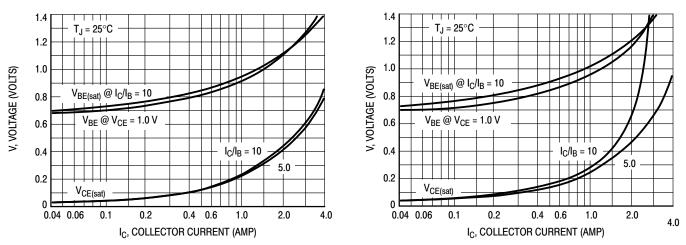


Figure 5. "On" Voltages

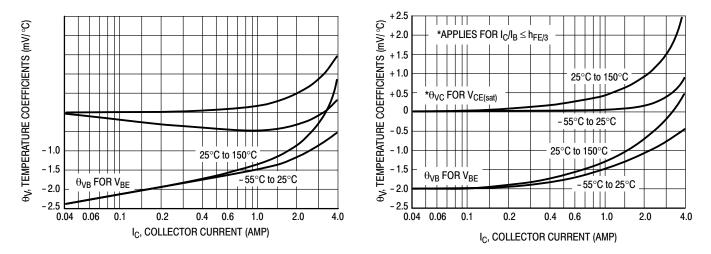
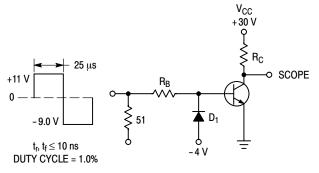


Figure 6. Temperature Coefficients



 R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS D_1 MUST BE FAST RECOVERY TYPE, e.g.: 1N5825 USED ABOVE $I_B\approx 100$ mA MSD6100 USED BELOW $I_B\approx 100$ mA FOR PNP TEST CIRCUIT, REVERSE ALL POLARITIES

1K 500 300 200 100 t, TIME (ns) 50 30 20 10 $I_C/I_B = 10$ $T_J = 25^{\circ}C$ NPN MJD243 3 2 PNP MJD253 0.01 0.02 0.03 0.05 0.1 0.2 0.3 0.5 10 IC, COLLECTOR CURRENT (AMPS)

Figure 8. Turn-On Time

Figure 7. Switching Time Test Circuit

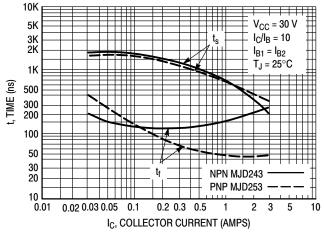


Figure 9. Turn-Off Time

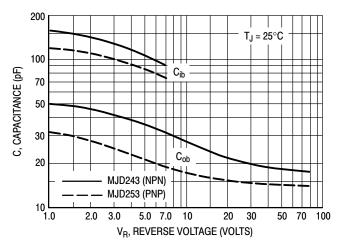


Figure 10. Capacitance

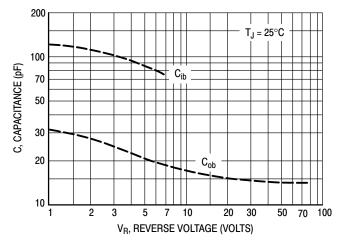


Figure 11. Capacitance

ORDERING INFORMATION

Device	Package Type	Package	Shipping [†]
MJD243G	DPAK-3 (Pb-Free)	369C	75 Units / Rail
MJD243T4G	DPAK-3 (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD243T4G*	DPAK-3 (Pb-Free)	369C	2,500 / Tape & Reel
MJD253-1G	IPAK (Pb–Free)	369D	75 Units / Rail
MJD253T4G	DPAK-3 (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD253T4G*	DPAK-3 (Pb-Free)	369C	2,500 / Tape & Reel

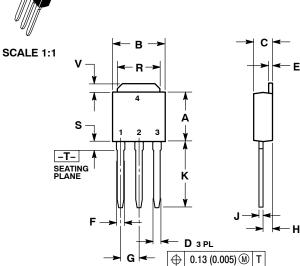
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP

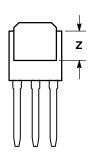
MECHANICAL CASE OUTLINE





DATE 15 DEC 2010





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090	BSC	2.29	BSC
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155		3.93	

MARKING DIAGRAMS

1:	s
BASE	
COLLECTOR	
EMITTER	
COLLECTOR	
	BASE COLLECTOR EMITTER

STYLE 5: PIN 1. GATE

2. ANODE CATHODE

ANODE

STYLE 2: PIN 1. GATE 2. DRAIN SOURCE 3 DRAIN

STYLE 6: PIN 1. MT1 2. MT2 3. GATE

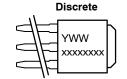
MT2

STYLE 3: PIN 1. ANODE 2. CATHODE 3 ANODE 4. CATHODE

STYLE 7: PIN 1. GATE 2. COLLECTOR

3. EMITTER COLLECTOR STYLE 4: PIN 1. CATHODE ANODE
 GATE

4. ANODE



WW



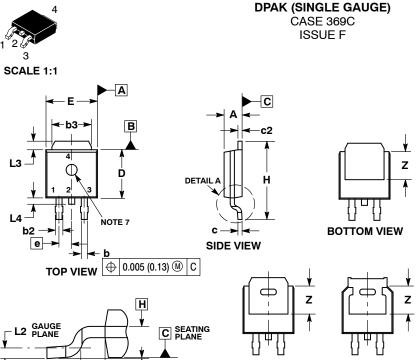
xxxxxxxxx = Device Code Α = Assembly Location IL = Wafer Lot Υ = Year

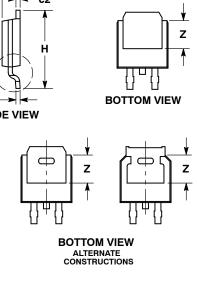
= Work Week

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DESCRIPTION:	IPAK (DPAK INSERTION M	IOUNT)	PAGE 1 OF 1

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STYLE 5:

STYLE 4:

STILE I.	STILE 2.	311	LE 3.	31	TLE 4.	STILE 5.
PIN 1. BASE	PIN 1. GA	ΓE PII	N 1. ANODE	F	PIN 1. CATHODE	PIN 1. GATE
COLLE	CTOR 2. DR	AIN	CATHOI	DE	ANODE	2. ANODE
EMITTE	R 3. SO	URCE	ANODE		GATE	CATHODE
COLLE	CTOR 4. DR	AIN	4. CATHO	DE	ANODE	4. ANODE
STYLE 6:	STYLE 7:	STYLE 8:		STYLE 9:		STYLE 10:
PIN 1. MT1	PIN 1. GATE	PIN 1. N/		PIN 1. A		PIN 1. CATHODE
2. MT2	COLLECTOR	2. CA	ATHODE	2. C	ATHODE	2. ANODE
GATE	EMITTER	3. AN	NODE	3. R	ESISTOR ADJUST	CATHODE
4. MT2	COLLECTOR	R 4. CA	ATHODE	4. C	ATHODE	4. ANODE

STYLE 3:

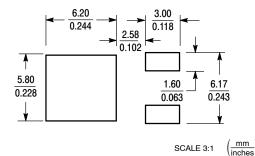
SOLDERING FOOTPRINT*

Α1

STYLE 2:

DETAIL A ROTATED 90° CW

STYLE 1:



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DATE 21 JUL 2015

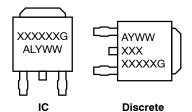
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: INCHES.
- 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-
- MENSIONS b3, L3 and Z.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
 5. DIMENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.

 6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
е	0.090	BSC	2.29	BSC
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

GENERIC MARKING DIAGRAM*



XXXXXX = Device Code = Assembly Location Α L = Wafer Lot

Υ = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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